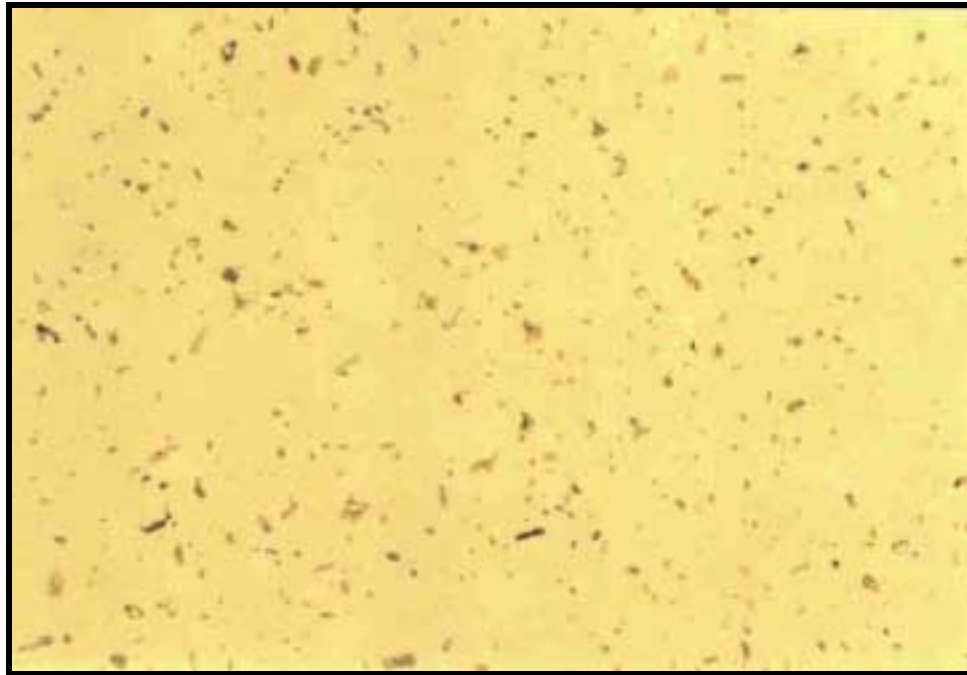


MetPrep Preparation Procedure – No 151



Sintered Silicon Carbide

	Surface	Abrasive	Pressure		Speed – Dir	Time
			Psi	N		
Primary Grinding Stage	Fixed Diamond	40 µm MB	5	25	500 – Comp	Until Planar

	Surface	Abrasive	Pressure		Speed – Dir	Time
			Psi	N		
Additional Grinding Stages	Fixed Diamond	10 µm RB	5	25	500 – Comp	6 mins
	Planocloth	6 µm (WB) PCD Diamond	5	25	250 – Comp	4 mins

	Surface	Abrasive	Pressure		Speed – Dir	Time
			Psi	N		
Polishing Stage	Planocloth	1 µm (WB) PCD Diamond & 0.06 µm Silco	5	25	100 – Contra	10 mins